

ABSTRACT

Aspects of the present invention provide for a novel photomask for patterning features for an integrated circuit, the photomask including a first area transmitting light in a first phase surrounded by second area, the second area transmitting light in a second phase, the second phase opposite the first phase. No blocking material separates the first area from the second area. After development of photoresist, the transition between the first and second area causes formation of a residual photoresist feature on the photoresist surface due to phase canceling of light. If the first area is small enough, it is nonprinting, ie., the opposite sides of the residual photoresist feature formed at its perimeter merge, forming a contiguous photoresist feature, and thus a corresponding patterned feature after etch.